

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed for industrial and consumer applications such as temperature, light and speed control; process and remote controls; warning systems; capacitive discharge circuits and MPU interface.

Features

- Center Gate Geometry for Uniform Current Density
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Low Trigger Currents, 200 μA Maximum for Direct Driving from **Integrated Circuits**
- These are Pb-Free Devices*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|--|---------------------------------------|-------------------|------------------|
| | V _{DRM,} V _{RRM} | 100 400 600 | > |
| On-State RMS Current (180° Conduction Angles; T _C = 83°C) | I _{T(RMS)} | 8.0 | Α |
| Peak Non-Repetitive Surge Current (1/2 Cycle, 60 Hz, T _J = 110°C) | I _{TSM} | 100 | Α |
| Circuit Fusing Considerations (t = 8.3 ms) | I ² t | 40 | A ² s |
| Forward Peak Gate Voltage (t \leq 10 μ s, T _C = 83°C) | V _{GM} | ±5.0 | V |
| Forward Peak Gate Current (t \leq 10 μ s, T _C = 83°C) | I _{GM} | 1.0 | Α |
| Forward Peak Gate Power (t \leq 10 μ s, T _C = 83°C) | P _{GM} | 5.0 | W |
| Average Gate Power (t = 8.3 ms, T _C = 83°C) | P _{G(AV)} | 0.75 | W |
| Operating Junction Temperature Range | TJ | -40 to +110 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |
| Mounting Torque | _ | 8.0 | in. lb. |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be

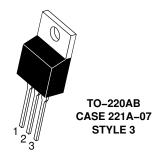


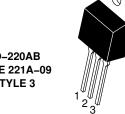
ON Semiconductor®

www.onsemi.com

SCRs 8 AMPERES RMS 100 thru 600 VOLTS







TO-220AB **CASE 221A-09** STYLE 3

| PIN ASSIGNMENT | | | | |
|----------------|--|--|--|--|
| Cathode | | | | |
| Anode | | | | |
| Gate | | | | |
| Anode | | | | |
| | | | | |

MARKING AND ORDERING INFORMATION

See detailed marking, ordering, and shipping information in the package dimensions section on page 4 of this data sheet.

assumed, damage may occur and reliability may be affected.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|----------------|-----|------|
| Thermal Resistance, Junction-to-Case | $R_{	heta JC}$ | 2.2 | °C/W |
| Thermal Resistance, Junction-to-Ambient | $R_{	heta JA}$ | 60 | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Secs | TL | 260 | °C |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

| Characteristic | Symbol | Min | Тур | Max | Unit | |
|---|---|-------------------------------------|--------|--------|-----------|--------------------------|
| OFF CHARACTERISTICS | | • | | • | | |
| Peak Repetitive Forward or Reverse Blocking Current (Note 2) (V_{AK} = Rated V_{DRM} or V_{RRM} ; R_{GK} = 1 $k\Omega$) | T _J = 25°C T _J = 110°C | I _{DRM} , I _{RRM} | _ _ | - - | 10 500 | μ Α μ Α |
| High Logic Level Supply Current from V _{CC} | | Іссн | 4 | 4 | μА | μΑ |
| ON CHARACTERISTICS | | • | | | | |
| Peak Forward On-State Voltage $(I_{TM} = 16 \text{ A Peak, Pulse Width} \le 1 \text{ ms, Duty Cycle} \le 2\%)$ | | V _{TM} | - | 1.7 | 2.0 | V |
| Gate Trigger Current (Continuous dc) (Note 3) $(V_D = 12 \text{ V}, R_L = 100 \Omega)$ | | I _{GT} | - | 30 | 200 | μΑ |
| Gate Trigger Voltage (Continuous dc) (Note 3) $(V_D = 12 \text{ V}, R_L = 100 \Omega)$ | | V _{GT} | - | 0.5 | 1.5 | V |
| Gate Non-Trigger Voltage (V _D = 12 Vdc, R _L = 100 Ω, T _J = 110°C) | | V _{GD} | 0.1 | - | - | V |
| Holding Current ($V_D = 12 \text{ V}$, Initiating Current = 200 mA, $R_{GK} = 1 \text{ k}\Omega$) | | lн | - | - | 6.0 | mA |
| Gate Controlled Turn-On Time (V _D = Rated V _{DRM} , I _{TM} = 16 A, I _G = 2 mA) | t _{gt} | - | 1.0 | - | μs | |
| DYNAMIC CHARACTERISTICS | | | | | • | |
| Critical Rate-of-Rise of Off-State Voltage $(V_D = Rated\ V_{DRM},\ R_{GK} = 1\ k\Omega,\ T_J = 110^{\circ}C,\ Exponential\ Wave$ | dv/dt | - | 10 | _ | V/μs | |

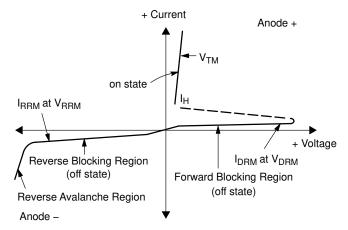
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Ratings apply for negative gate voltage or R_{GK} = 1 kΩ. Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

3. R_{GK} current not included in measurement.

Voltage Current Characteristic of SCR

| Symbol | Parameter |
|------------------|---|
| V_{DRM} | Peak Repetitive Off State Forward Voltage |
| I _{DRM} | Peak Forward Blocking Current |
| V_{RRM} | Peak Repetitive Off State Reverse Voltage |
| I _{RRM} | Peak Reverse Blocking Current |
| V_{TM} | Peak On State Voltage |
| I _H | Holding Current |



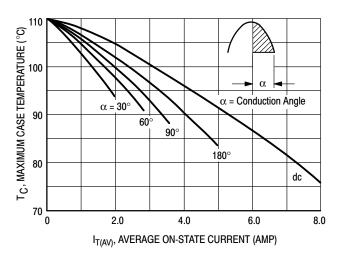


Figure 1. Average Current Derating

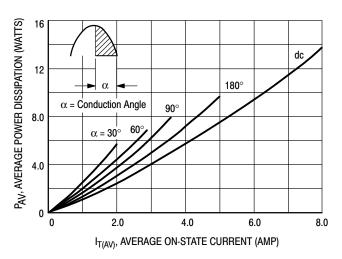


Figure 2. On-State Power Dissipation

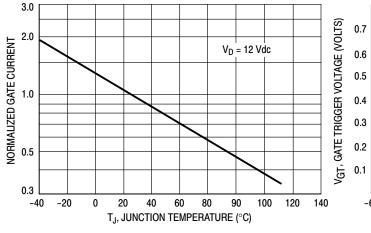


Figure 3. Normalized Gate Current

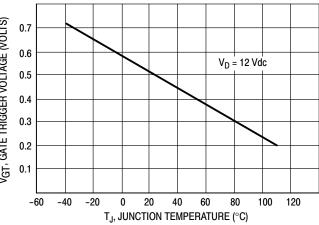
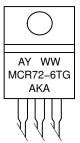


Figure 4. Gate Voltage

MARKING DIAGRAMS

TO-220AB CASE 221A-07

AY WW MCR72-xG AKA TO-220AB CASE 221A-09



A = Assembly Location

Y = Year WW = Work Week MCR72-x = Device Code x = 3, 6, 8, or 8T

G = Pb-Free Package AKA = Diode Polarity A = Assembly Location

Y = Year

WW = Work Week

MCR72-6T = Device Code

G = Pb-Free Package

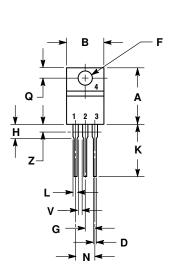
AKA = Diode Polarity

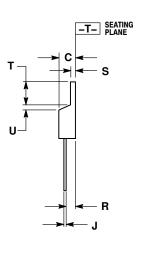
ORDERING INFORMATION

| Device | Package | Shipping |
|-----------|-----------------------|-----------------|
| MCR72-3G | TO-220AB (Pb-Free) | 500 Units / Box |
| MCR72-6G | TO-220AB (Pb-Free) | 500 Units / Box |
| MCR72-6TG | TO-220AB (Pb-Free) | 50 Units / Rail |
| MCR72-8G | TO-220AB (Pb-Free) | 500 Units / Box |
| MCR72-8TG | TO-220AB (Pb-Free) | 50 Units / Rail |

PACKAGE DIMENSIONS

TO-220 CASE 221A-07 ISSUE O





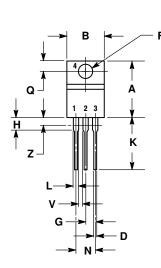
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

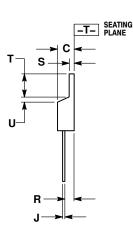
| | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.405 | 9.66 | 10.28 |
| С | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.022 | 0.36 | 0.55 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ٧ | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

- STYLE 3:
 PIN 1. CATHODE
 2. ANODE
 3. GATE
 4. ANODE

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

| | INCHES | | MILLIN | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.415 | 9.66 | 10.53 |
| С | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ٧ | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

STYLE 3:

PIN 1. CATHODE

- 2. ANODE
- GATE
- ANODE

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